

Stanford

Zikang Tong

Ph.D. Student in Electrical Engineering, admitted Autumn 2017

Publications

PUBLICATIONS

- **A Multiresonant Gate Driver for High-Frequency Resonant Converters** *IEEE TRANSACTIONS ON INDUSTRIAL ELECTRONICS*
Gu, L., Tong, Z., Liang, W., Rivas-Davila, J.
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- **On the Techniques to Utilize SiC Power Devices in High- and Very High-Frequency Power Converters** *IEEE TRANSACTIONS ON POWER ELECTRONICS*
Tong, Z., Gu, L., Ye, Z., Surakitbovorn, K., Rivas-Davila, J.
2019; 34 (12): 12181–92
- **Output Capacitance Loss Characterization of Silicon Carbide Schottky Diodes** *IEEE JOURNAL OF EMERGING AND SELECTED TOPICS IN POWER ELECTRONICS*
Tong, Z., Zulauf, G., Xu, J., Plummer, A. D., Rivas-Davila, J.
2019; 7 (2): 865–78
- **Empirical Circuit Model for Output Capacitance Losses in Silicon Carbide Power Devices**
Tong, Z., Park, S., Rivas-Davila, J., IEEE
IEEE.2019: 998–1003
- **Gate Drive for Very Fast Resonant Conversion using SiC Switch**
Tong, Z., Gu, L., Surakitbovorn, K., Rivas-Davila, J. M., IEEE
IEEE.2019: 6647–54
- **3-D Printed Air-Core Toroidal Transformer for High-Frequency Power Conversion**
Tong, Z., Braun, W. D., Rivas-Davila, J. M., IEEE
IEEE.2019
- **Active Power Device Selection in High- and Very-High-Frequency Power Converters** *IEEE Transactions on Power Electronics*
Zulauf, G. D., Tong, Z., Plummer, J. D., Rivas-Davila, J. M.
2018: 1
- **A Study on Off-State Losses in Silicon-Carbide Schottky Diodes**
Tong, Z., Zulauf, G., Rivas-Davila, J., IEEE
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- **Considerations for Active Power Device Selection in High- and Very-High-Frequency Power Converters**
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